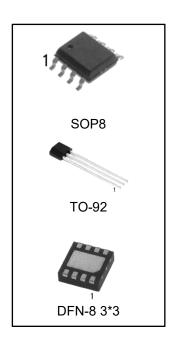


Description

The LM236 and LM336 are precision 2.5V regulator diodes. These voltage reference monolithic ICs operate like 2.5V zener diodes with a low temperature coefficient and a dynamic impedance of 0.2 Ω . A third pin enables adjusting the reference voltage and the temperature coefficient.

Features

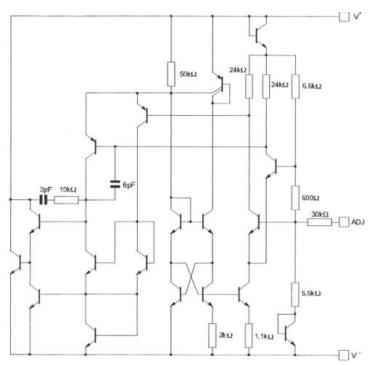
- Low temperature coefficient
- Wide operating current of 400μA to 10 mA
- 0.2Ω dynamic impedance
- ± 1% initial tolerance available
- Guaranteed temperature stability
- Fast turn-on



Ordering Information

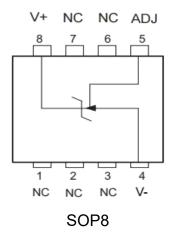
DEVICE	Package Type	MARKING	Packing	Packing Qty
LM236M-2.5/TR	SOP8	236-2.5	Reel	2500pcs/reel
LM336M-2.5/TR	SOP8	DP8 336-2.5 Reel		2500pcs/reel
LM236Z-2.5	TO-92	LM236-2.5	Tape	1000pcs/box
LM336Z-2.5	TO-92	LM336-2.5	Tape	1000pcs/box
LM236DQ-2.5/TR	DFN-8 3*3	236-2.5	Reel	2500pcs/reel
LM336DQ-2.5/TR	DFN-8 3*3	336-2.5	Reel	2500pcs/reel

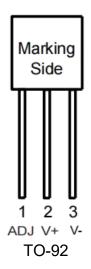
Schematic Diagram

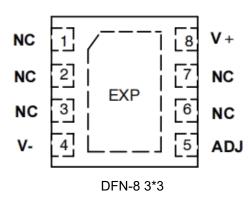




Pin Connections







Absolute Maximum Ratings

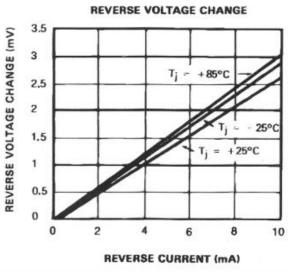
Symbol	Parameter	LM336	Unit
	Current		
IRIF	Reverse	15	mA
	Forward	10	
Toper	Operating Free-air Temperature Range	LM336-2.5: 0 to +70	°C
	Operating Tree-air Temperature Mange	LM236-2.5: -40 to +85	°C
T _{Stg}	Storage Temperature Range	-65 to +150	°C

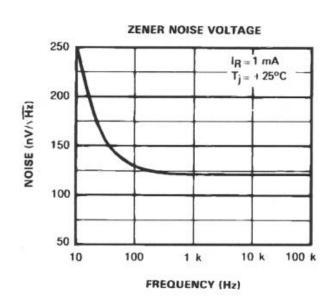
Electrical Characteristics

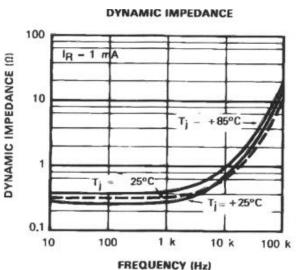
Council of	Develope	LM	l lm!4		
Symbol	Parameter Parameter	Min.	Тур.	Max.	Unit
	Reference Breakdown Voltage				
VR	T_{amb} = +25°C, I_R = 1mA	2.44	2.49	2.54	V
	LM336				
	Reverse Breakdown Voltage Change with Current				
ΔVR	$400\mu\text{A} \le I_R \le 10\text{mA}$				
ΔVR	$T_{amb} = +25^{\circ}C$	-	2.6	10	mV
	$T_{min.} \le T_{amb} \le T_{max.}$		3	12	
	Reverse Dynamic Impedance (I _R = 1mA)				
Z _D	$T_{amb} = +25^{\circ}C$	-	0.2	1	Ω
	$T_{min.} \le T_{amb} \le T_{max.}$		0.4	1.4	
KVT	Temperature Stability (V_R = 2.49V, I_R = 1mA)	-	1.8	6	mV
K _{VH}	Long Term Stability (T _{amb} = +25°C ±0.1°C, I _R = 1mA)	-	20	-	ppm

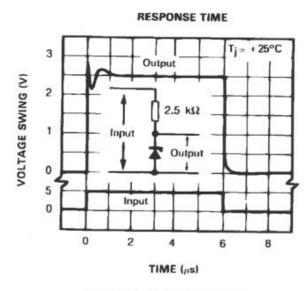


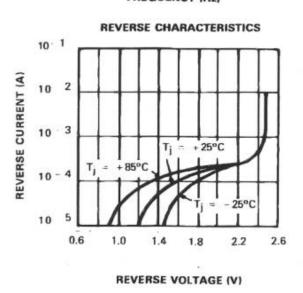
Typical Performance Characteristics

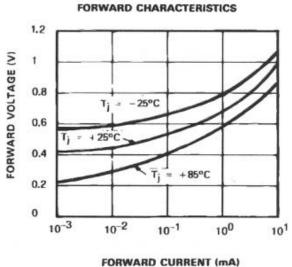






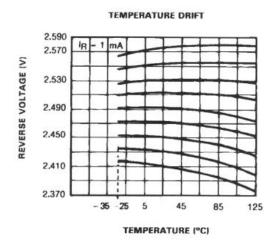








Typical Performance Characteristics (Continued)



Application Hints

The LM336 voltage references are easier to use than zener diodes. Their low impedance and wide current range facilitate biasing in any circuits. Besides, the breakdown voltage or the temperature coefficient can be adjusted so as to optimize the performance of the circuit.

Figure 1 represents a LM336 with a $10k\Omega$ potentiometer to adjust the reverse breakdown voltage which can be adjusted without altering the temperature coefficient of the circuit. The adjustment range is generally sufficient to adjust the initial tolerance of the circuit and the inaccuracy of the amplifier circuit.

To obtain a lower temperature coefficient two diodes can be connected in series as indicated in Figure 2.

When the circuit is adjusted to 2.49V the temperature coefficient is minimized. For a correct temperature coefficient, the diodes should be at the same ambient temperature as the LM336. The value of R1 is not critical (2-20k Ω).

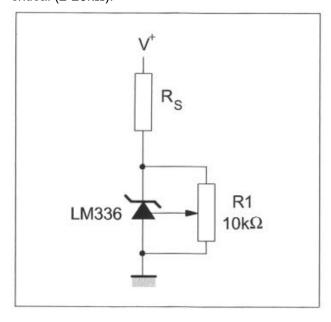


FIGURE1.LM336 with Pot for Adjustment of Breakdown Voltage

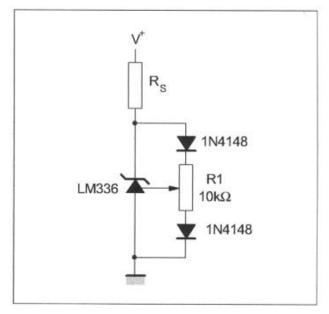


FIGURE 2. Temperature Coefficient Adjustment



Typical Applications

Figure 3:2.5V Reference

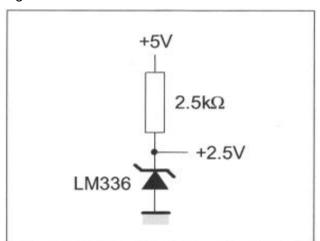


Figure 4: Wide Input Range Reference

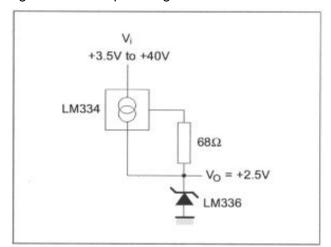


Figure 5 : Precision Power Regulator with Low Temperature Coefficient

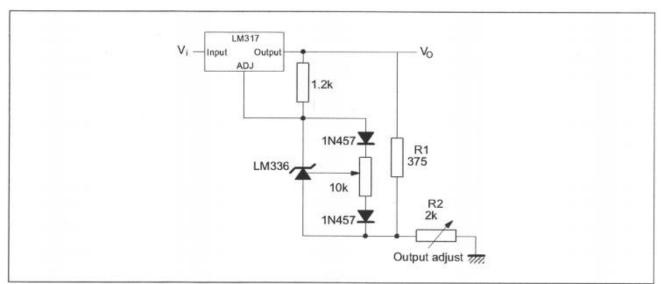


Figure 5 : Adjustable Shunt Regulator

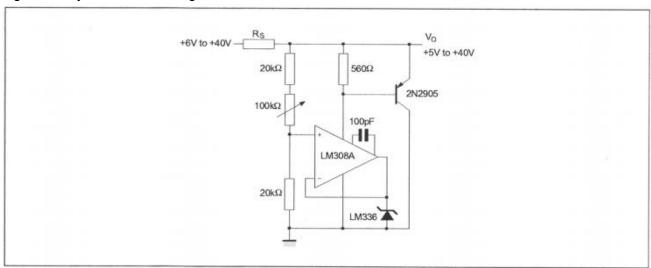




Figure 7 :Linear Ohmmeter

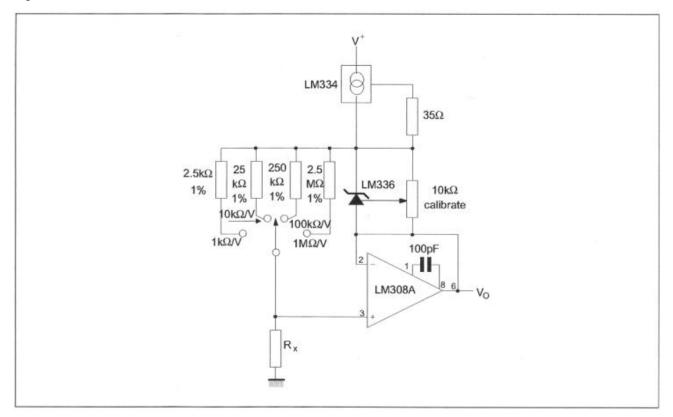


Figure 8 :Bipolar Output Reference

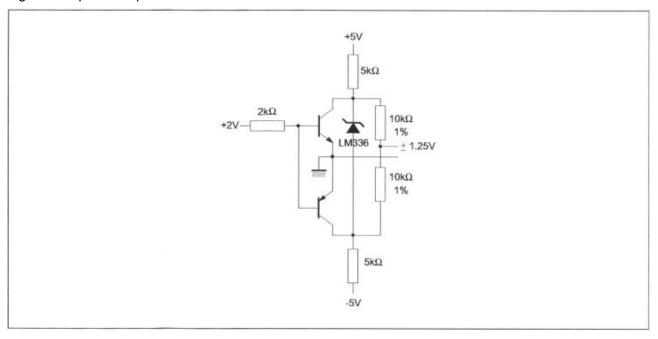




Figure 9:5V Buffered Reference

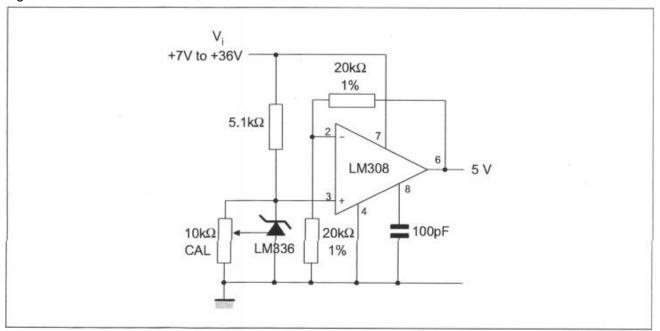
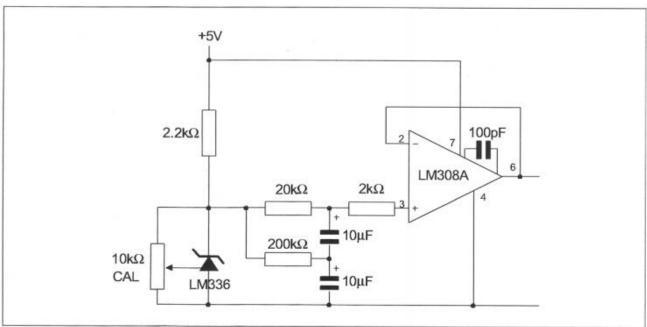


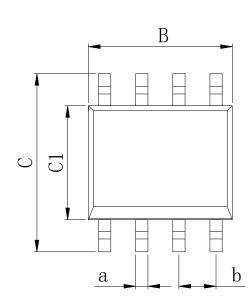
Figure 10 : Low Noise Buffered Reference

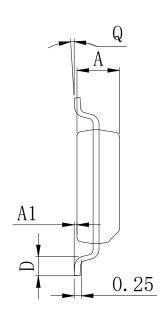




Physical Dimensions

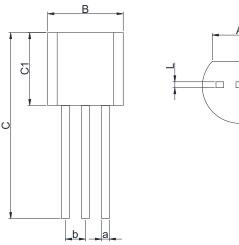
SOP8

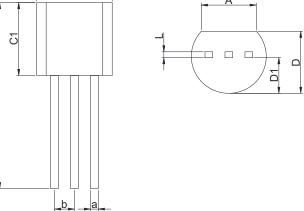




Dimensions In Millimeters(SOP8)										
Symbol:	Α	A1	В	С	C1	D	Q	а	b	
Min:	1.35	0.05	4.90	5.80	3.80	0.40	0°	0.35	1.27 BSC	
Max:	1.55	0.20	5.10	6.20	4.00	0.80	8°	0.45	1.27 650	

TO-92



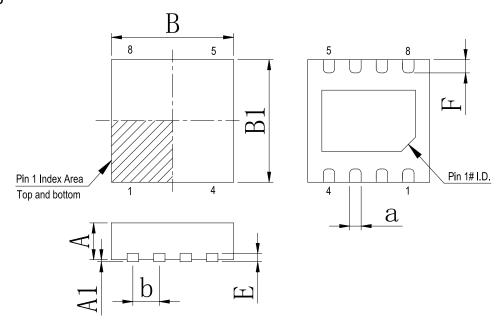


Dimensions In Millimeters(TO-92)									
Symbol:	Α	В	С	C1	D	D1	L	а	b
Min:	3.43	4.44	11.2	4.32	3.17	2.03	0.33	0.40	1.27BSC
Max:	3.83	5.21	12.7	5.34	4.19	2.67	0.42	0.52	1.27B3C



Physical Dimensions

DFN-8 3*3



Dimensions In Millimeters(DFN-8 3*3)										
Symbol:	А	A1	В	B1	Е	F	а	b		
Min:	0.85	0.00	2.90	2.90	0.20	0.30	0.20	0.65.000		
Max:	0.95	0.05	3.10	3.10	0.25	0.50	0.34	0.65 BSC		



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